

STB70N10F4, STD70N10F4 STP70N10F4, STW70N10F4

N-channel 100 V, 0.015 Ω 60 A, STripFET[™] DeepGATE[™] Power MOSFET in TO-220, DPAK, TO-247, D²PAK

Features

Туре	V _{DSS}	R _{DS(on)} max	I _D
STB70N10F4	100 V	< 0.0195 Ω	65 A
STD70N10F4	100 V	< 0.0195 Ω	60 A
STP70N10F4	100 V	< 0.0195 Ω	65 A
STW70N10F4	100 V	< 0.0195 Ω	65 A

- Exceptional dv/dt capability
- Extremely low on-resistance R_{DS(on)}
- 100% avalanche tested

Application

Switching applications

Description

This STripFET™ DeepGATE™ Power MOSFET technology is among the latest improvements, which have been especially tailored to minimize on-state resistance, with a new gate structure, providing superior switching performance.

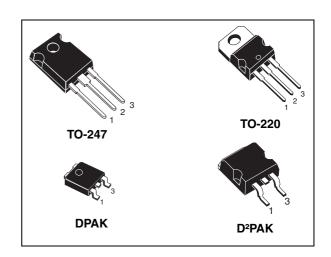


Figure 1. Internal schematic diagram

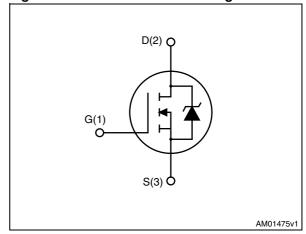


Table 1. Device summary

Order codes	Marking	Package	Packaging
STB70N10F4	70N10F4	D²PAK	Tape and reel
STD70N10F4	70N10F4	DPAK	Tape and reel
STP70N10F4	70N10F4	TO-220	Tube
STW70N10F4	70N10F4	TO-247	Tube

Contents STB/D/P/W70N10F4

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STB/D/P/W70N10F4 Electrical ratings

1 Electrical ratings

Table 2. Absolute maximum ratings

		Value		
Symbol	Parameter	TO-220, TO-247, D ² PAK	DPAK	Unit
V_{DS}	Drain-source voltage (V _{GS} = 0)	100		V
V _{GS}	Gate-source voltage	± 20		V
I _D	Drain current (continuous) at T _C = 25 °C	65	60	Α
I _D	Drain current (continuous) at T _C = 100 °C	46	43	Α
I _{DM} ⁽¹⁾	Drain current (pulsed)	260 240		Α
P _{TOT}	Total dissipation at T _C = 25 °C	150	125	W
	Derating factor	1 0.83		W/°C
E _{AS} (2)	Single pulse avalanche energy	120		mJ
T _{stg}	Storage temperature	- 55 to 175		°C
T _j	Max. operating junction temperature	- 55 10	173	

^{1.} Pulse width limited by safe operating area

Table 3. Thermal data

		Value		
Symbol Parameter		TO-220, TO-247, D ² PAK	DPAK	Unit
R _{thj-case}	Thermal resistance junction-case max	1 1.2		°C/W
R _{thj-a}	Thermal resistance junction-ambient max	62.5 50 ⁽¹⁾		°C/W
T _I	Maximum lead temperature for soldering purpose	300		°C

^{1.} When mounted on FR-4 board of 1 inch2, 2 oz Cu

^{2.} Starting $T_j = 25$ °C, $I_D = 32.5$ A, $V_{DD} = 45$ V

Electrical characteristics STB/D/P/W70N10F4

2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown voltage	$I_D = 250 \mu\text{A}, V_{GS} = 0$	100			٧
	Zero gate voltage	V _{DS} = max rating			1	μΑ
I _{DSS}	Drain current (V _{GS} = 0)	V _{DS} = max rating,T _C =125 °C			100	μΑ
I _{GSS}	Gate-body leakage current (V _{DS} = 0)	V _{GS} = ± 20 V			100	nA
V _{GS(th)}	Gate threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2		4	٧
R _{DS(on)}	Static drain-source on resistance	V _{GS} = 10 V, I _D = 30 A		0.015	0.0195	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
C _{iss}	Input capacitance			5800		pF
C _{oss}	Output capacitance	$V_{DS} = 25 \text{ V, f} = 1 \text{ MHz,}$	_	300	_	pF
C _{rss}	Reverse transfer capacitance	V _{GS} = 0		190		pF
Qg	Total gate charge	V _{DD} = 80 V, I _D = 65 A,		85		nC
Q_{gs}	Gate-source charge	V _{GS} = 10 V	-	20	-	nC
Q_{gd}	Gate-drain charge	(see Figure 16)		25		nC

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t _{d(on)}	Turn-on delay time Rise time	$V_{DD} = 50 \text{ V}, I_D = 30 \text{ A}$ $R_G = 4.7 \Omega V_{GS} = 10 \text{ V}$ (see Figure 15)	-	30 20	-	ns ns
t _{d(off)}	Turn-off-delay time Fall time	$V_{DD} = 50 \text{ V}, I_{D} = 30 \text{ A},$ $R_{G} = 4.7 \Omega, V_{GS} = 10 \text{ V}$ (see Figure 15)	-	65 20	-	ns ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Тур.	Max	Unit
I _{SD}	Source-drain current				60	Α
I _{SDM} ⁽¹⁾	Source-drain current (pulsed)		-		240	Α
V _{SD} ⁽²⁾	Forward on voltage	$I_{SD} = 60 \text{ A}, V_{GS} = 0$	-		1.5	V
t _{rr} Q _{rr} I _{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 60 \text{ A}, V_{DD} = 25 \text{ V}$ di/dt = 100 A/ μ s, $T_j = 150 ^{\circ}\text{C}$ (see Figure 17)	-	80 280 6.7		ns nC A

^{1.} Pulse width limited by safe operating area.

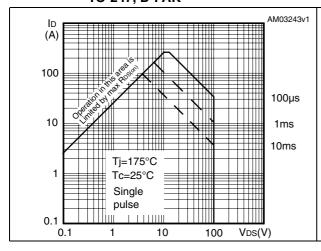
^{2.} Pulsed: Pulse duration = 300 μ s, duty cycle 1.5%

Electrical characteristics STB/D/P/W70N10F4

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220, TO-247, D²PAK

Figure 3. Thermal impedance for TO-220, TO-247, D2PAK



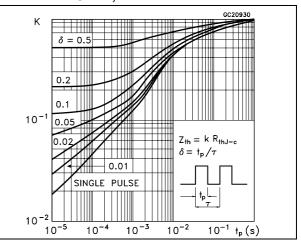
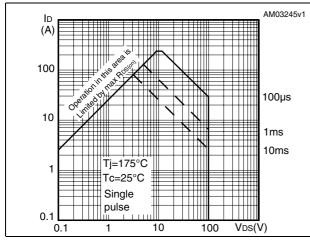


Figure 4. Safe operating area for DPAK

Figure 5. Thermal impedance for DPAK



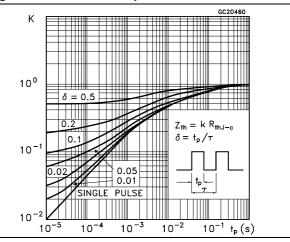
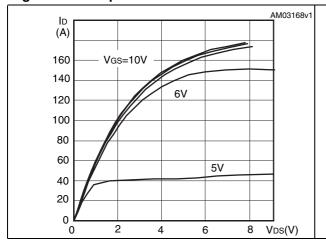
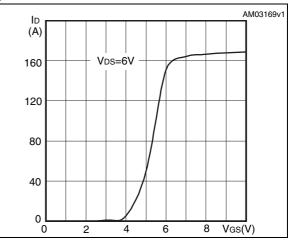


Figure 6. Output characteristics

Figure 7. Transfer characteristics





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Figure 8. Normalized B_{VDSS} vs temperature Figure 9. Static drain-source on resistance

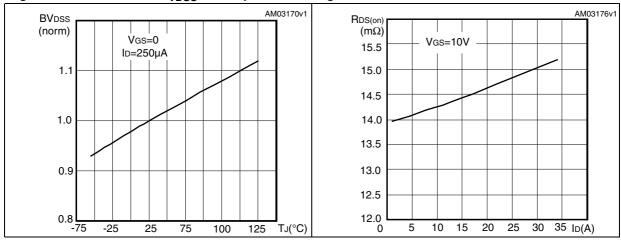


Figure 10. Gate charge vs gate-source voltage Figure 11. Capacitance variations

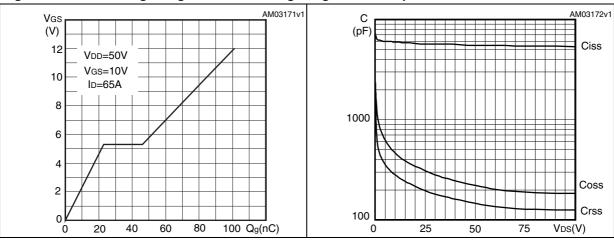
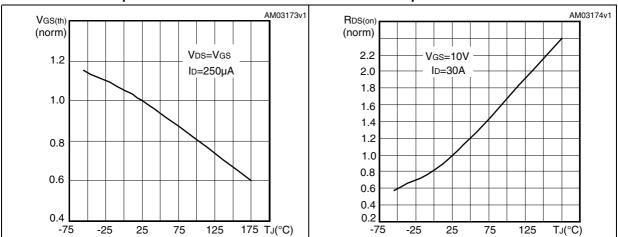
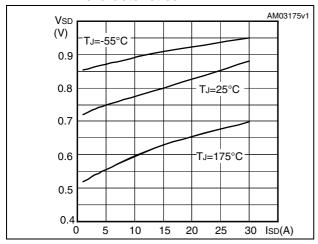


Figure 12. Normalized gate threshold voltage Figure 13. Normalized on resistance vs vs temperature temperature



Electrical characteristics STB/D/P/W70N10F4

Figure 14. Source-drain diode forward characteristics



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STB/D/P/W70N10F4 Test circuits

3 Test circuits

Figure 15. Switching times test circuit for resistive load

Figure 16. Gate charge test circuit

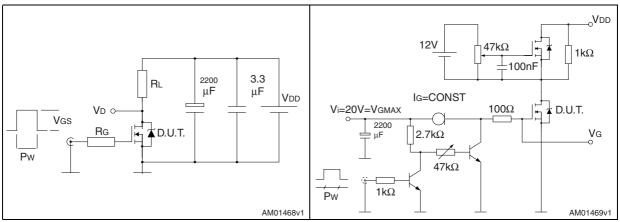


Figure 17. Test circuit for inductive load switching and diode recovery times

Figure 18. Unclamped inductive load test circuit

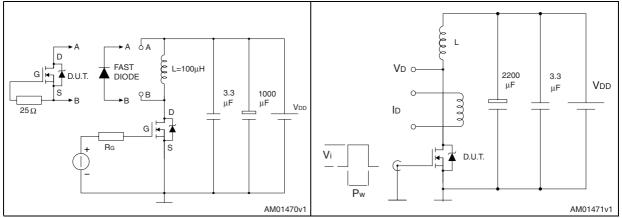
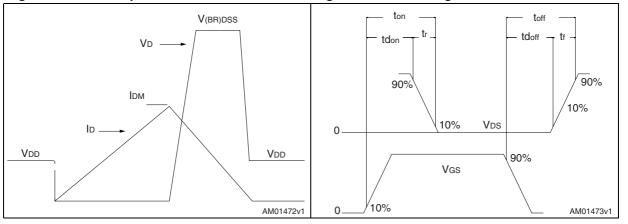


Figure 19. Unclamped inductive waveform

Figure 20. Switching time waveform



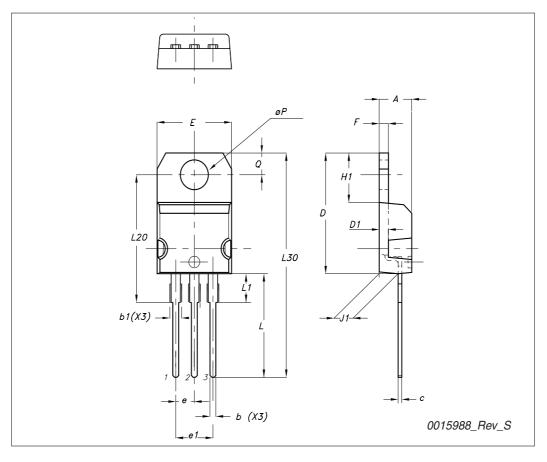
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

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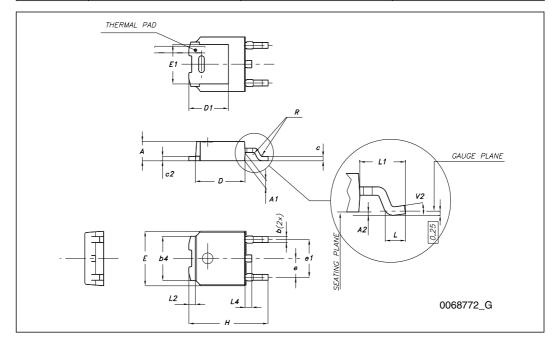
TO-220 type A mechanical data

Dim		mm	
DIIII	Min	Тур	Max
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
С	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
е	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95



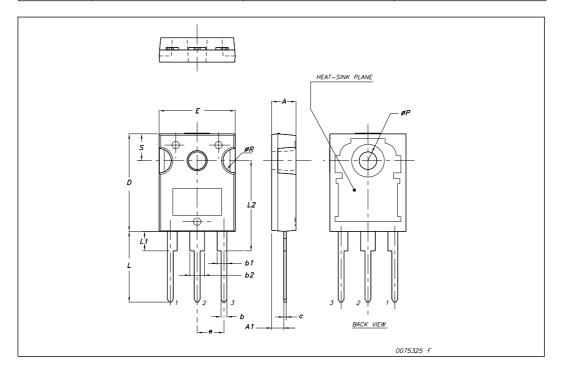
TO-252 (DPAK) mechanical data

DIM.		mm.	
	min.	typ	max.
Α	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
С	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
е		2.28	
e1	4.40		4.60
Н	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0 °		8 °



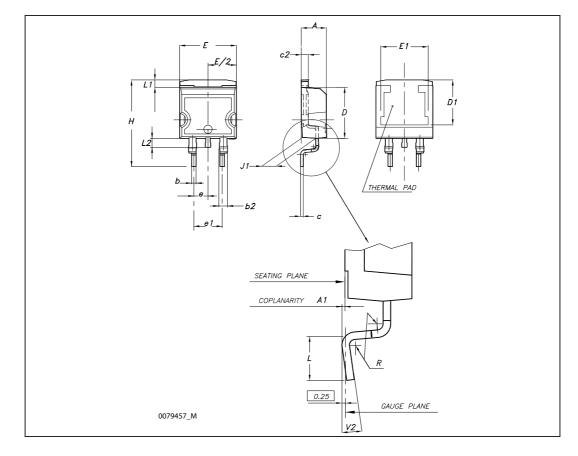
TO-247 Mechanical data

Dim.		mm.	
Diiii.	Min.	Тур	Max.
Α	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
С	0.40		0.80
D	19.85		20.15
Е	15.45		15.75
е		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
øΡ	3.55		3.65
øR	4.50		5.50
S		5.50	



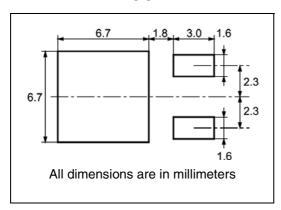
D²PAK (TO-263) mechanical data

Dim	mm			inch		
	Min	Тур	Max	Min	Тур	Max
Α	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
С	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
е		2.54			0.1	
e1	4.88		5.28	0.192		0.208
Н	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°

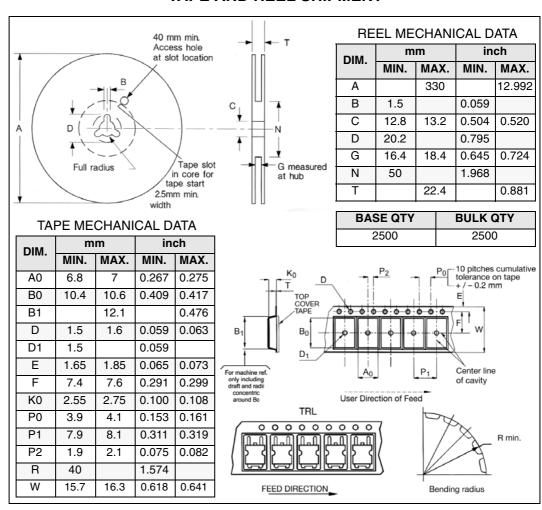


5 Packaging mechanical data

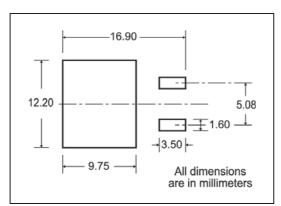
DPAK FOOTPRINT



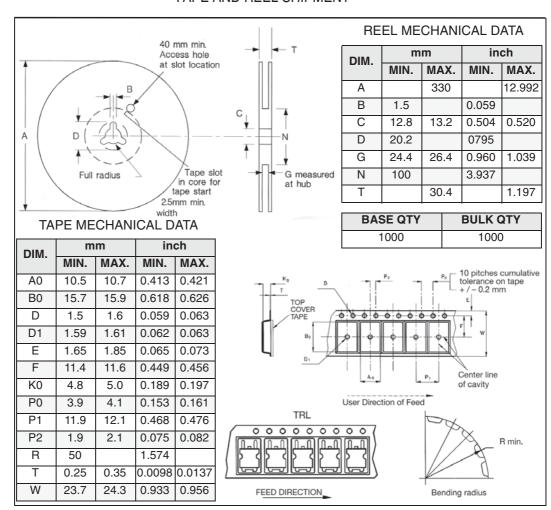
TAPE AND REEL SHIPMENT



D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



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STB/D/P/W70N10F4 Revision history

6 Revision history

Table 8. Document revision history

Date	Revision	Changes
12-Nov-2008	1	First release
14-Jan-2009	2	Added new package, mechanical data DPAK
09-Oct-2009	3	Added new package, mechanical data D ² PAK

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